



# PSMN1R3-80SSF

NextPower 80 V, 1.2 mOhm, 335 Amp, N-channel MOSFET in LPAK88 package

7 April 2025

Product data sheet

## 1. General description

NextPower 80 V, standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial and consumer applications.

## 2. Features and benefits

- Low  $Q_{rr}$  for higher efficiency and lower spiking
- 335 Amps  $I_{D(max)}$  continuous current rating
- Low  $Q_G \times R_{DSon}$  FOM for high efficiency switching applications
- Strong avalanche energy rating ( $E_{as}$ )
- Avalanche rated and 100% tested
- Ha-free and RoHS compliant LPAK88 package

## 3. Applications

- Synchronous rectifier in AC-DC and DC-DC
- Primary side switch in DC-DC
- BLDC motor control
- Full-bridge and half-bridge applications
- Battery protection

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>	[1]	-	-	335	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>		-	-	500	W
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>		-	1	1.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; <a href="#">Fig. 13</a>		-	1.6	2.2	mΩ
Dynamic characteristics							
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		10	29	67	nC
Q <sub>G(tot)</sub>	total gate charge			82	164	246	nC
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 93 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(i)nit</sub> = 25 °C; unclamped; t <sub>p</sub> = 180 μs; <a href="#">Fig. 4</a>	[2]	-	-	867	mJ

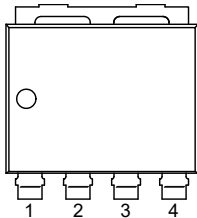
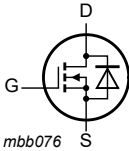
NextPower 80 V, 1.2 mOhm, 335 Amp, N-channel MOSFET in LPAK88 package

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
$Q_r$	recovered charge	$I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 40\text{ V}$ ; <a href="#">Fig. 18</a>	-	68	-	nC

- [1] 335 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 LPAK88 (SOT1235)	 mbb076
2	S	source		
3	S	source		
4	S	source		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R3-80SSF	LPAK88	plastic, single-ended surface-mounted package (LPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R3-80SSF	X1F3S80S

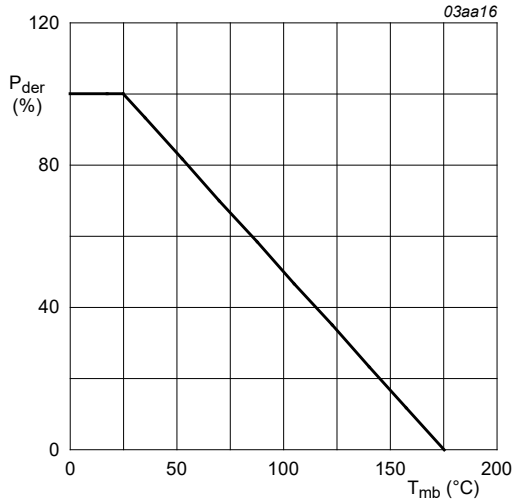
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

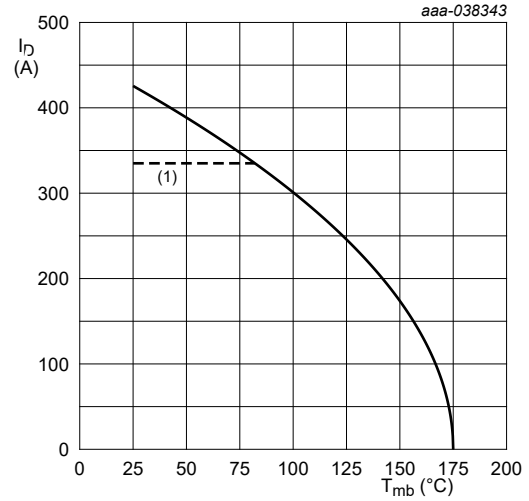
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	80	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	80	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; Fig. 1		-	500	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; Fig. 2	[1]	-	335	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; Fig. 2		-	301	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; Fig. 3		-	1703	A
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	335	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	1703	A
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 93 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; t <sub>p</sub> = 180 μs; Fig. 4	[2]	-	867	mJ
I <sub>AS</sub>	non-repetitive avalanche current	V <sub>sup</sub> = 80 V; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; R <sub>GS</sub> = 50 Ω	[2]	-	93	A

[1] 335 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.  
[2] Protected by 100% test.



$$P_{der} = \frac{P_{tot}}{P_{tot}(25^{\circ}\text{C})} \times 100\%$$

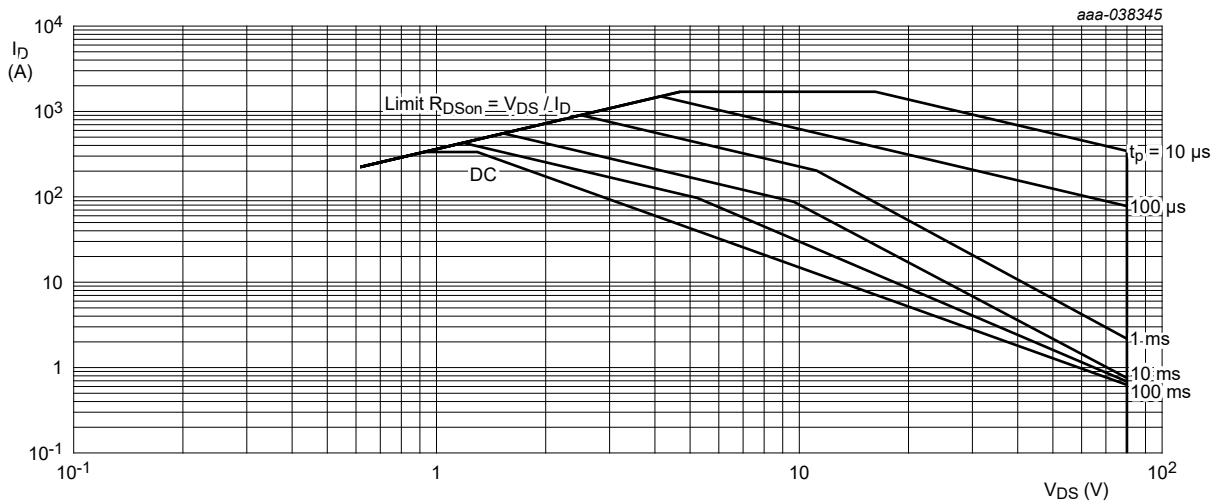
**Fig. 1.** Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq 10\text{ V}$

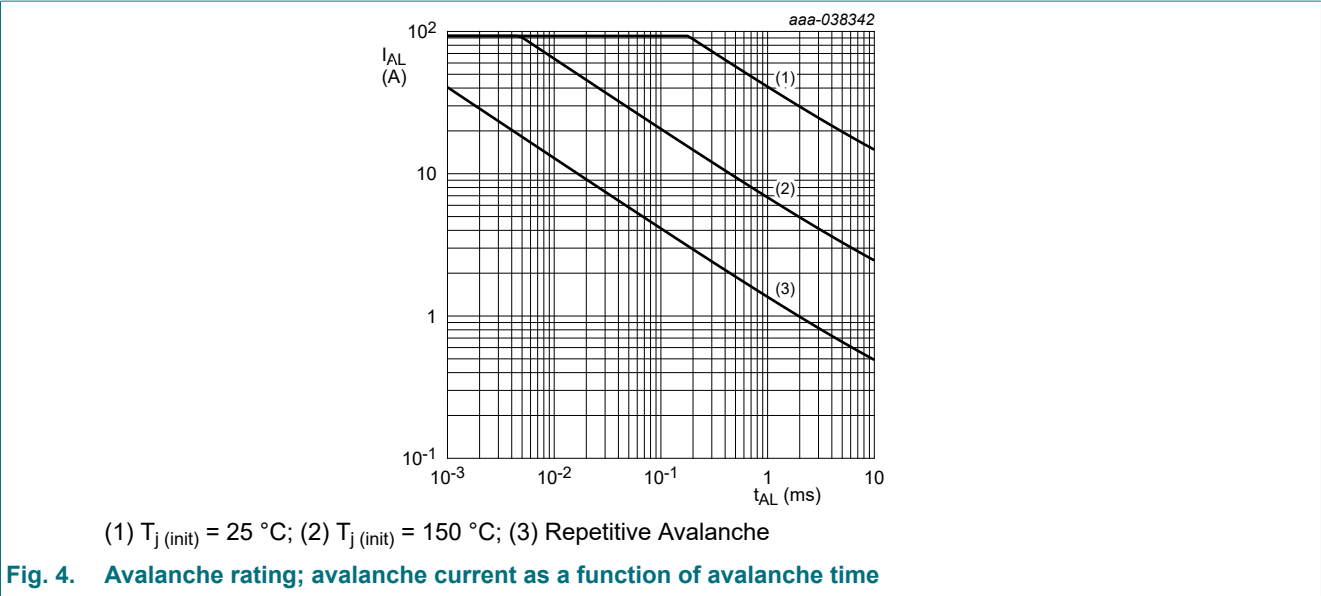
(1) 335 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

**Fig. 2.** Continuous drain current as a function of mounting base temperature



$T_{mb} = 25^{\circ}\text{C}$ ;  $I_{DM}$  is a single pulse

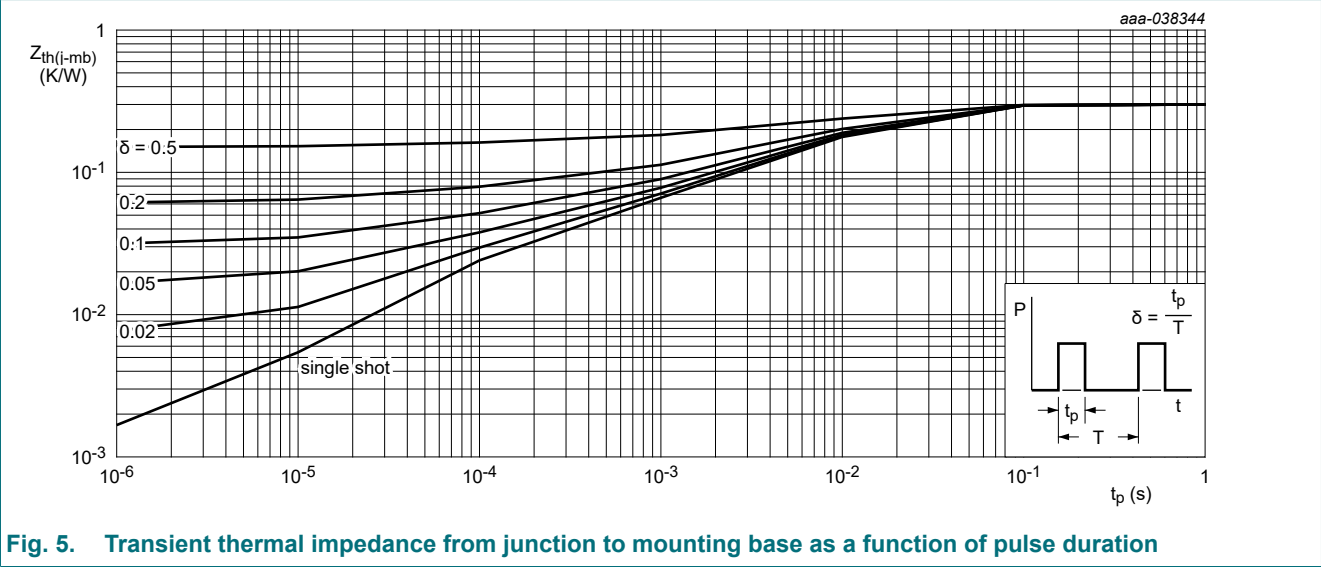
**Fig. 3.** Safe operating area; continuous and peak drain currents as a function of drain-source voltage

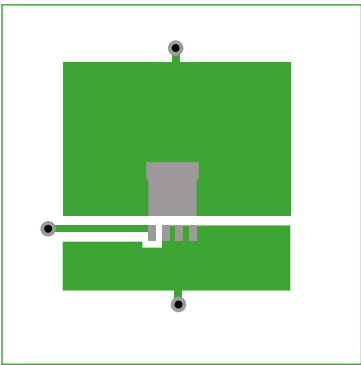


9. Thermal characteristics

Table 6. Thermal characteristics

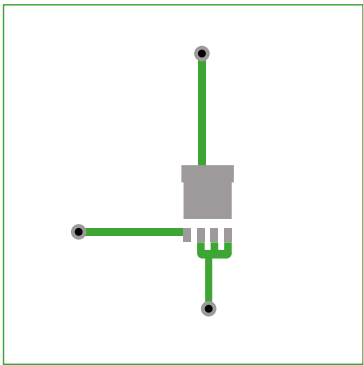
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 5</a>		-	0.23	0.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	<a href="#">Fig. 6</a>		-	35	-	K/W
		<a href="#">Fig. 7</a>		-	70	-	K/W





Copper square 25.4 mm square; 70 µm thick on FR4 board

Fig. 6. PCB layout for thermal resistance from junction to ambient



70 µm thick copper on FR4 board

Fig. 7. PCB layout with minimum footprint for thermal resistance from junction to ambient

## 10. Characteristics

**Table 7. Characteristics**

$T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise stated.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C		80	86	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = -55 °C		72	83	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = 25 °C; <a href="#">Fig. 11</a>		2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = 175 °C		-	1.7	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>J</sub> = -55 °C		-	3.4	-	V
ΔV <sub>GS(th)</sub> /ΔT	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>J</sub> ≤ 150 °C		-	-7.9	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	0.03	1	μA
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 125 °C		-	8	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C		-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 12</a>		-	1	1.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 105 °C; <a href="#">Fig. 13</a>		-	1.6	2.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>J</sub> = 175 °C; <a href="#">Fig. 13</a>		-	2.2	2.8	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>J</sub> = 25 °C		0.5	1	2	Ω
Dynamic characteristics							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		82	164	246	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V		-	145	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		18	46	74	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge			-	32.5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge			-	13.5	-	nC
Q <sub>GD</sub>	gate-drain charge			10	29	67	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		-	4.2	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; f = 0.5 MHz; <a href="#">Fig. 16</a>		7134	11891	16647	pF
C <sub>oss</sub>	output capacitance			1058	2645	4761	pF
C <sub>rss</sub>	reverse transfer capacitance			19	97	223	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 40 V; R <sub>L</sub> = 1.6 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω		-	40	-	ns
t <sub>r</sub>	rise time			-	34	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	104	-	ns
t <sub>f</sub>	fall time			-	51	-	ns
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 17</a>		-	0.77	1	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;	-	57	-	ns
$Q_r$	recovered charge	$V_{DS} = 40\text{ V}$ ; <a href="#">Fig. 18</a>	-	68	-	nC

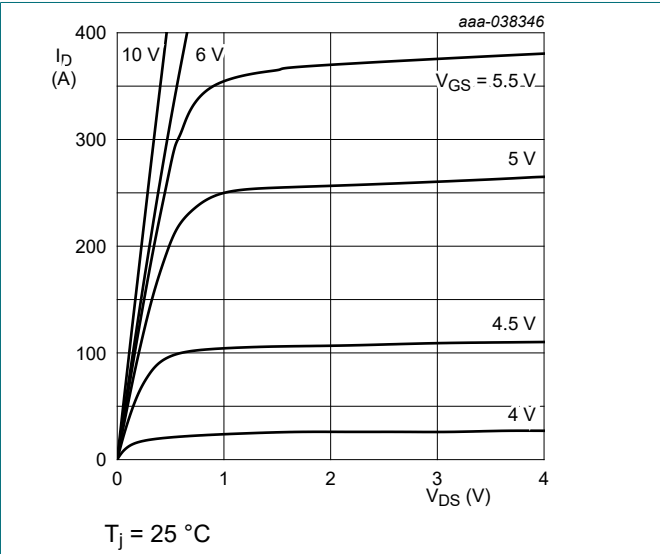


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

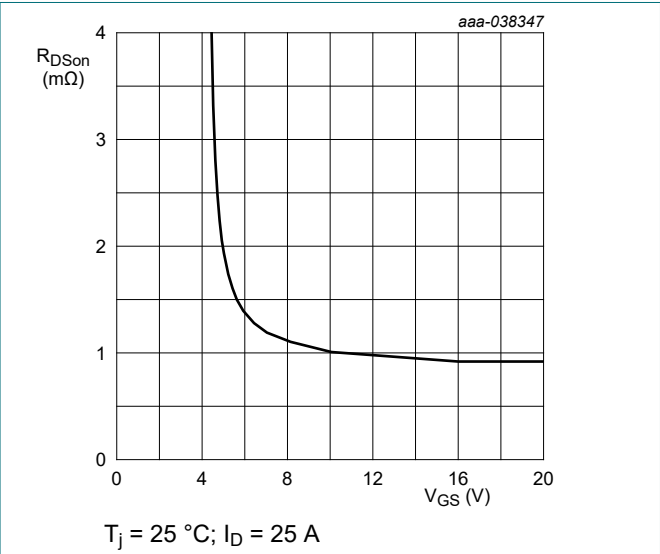


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

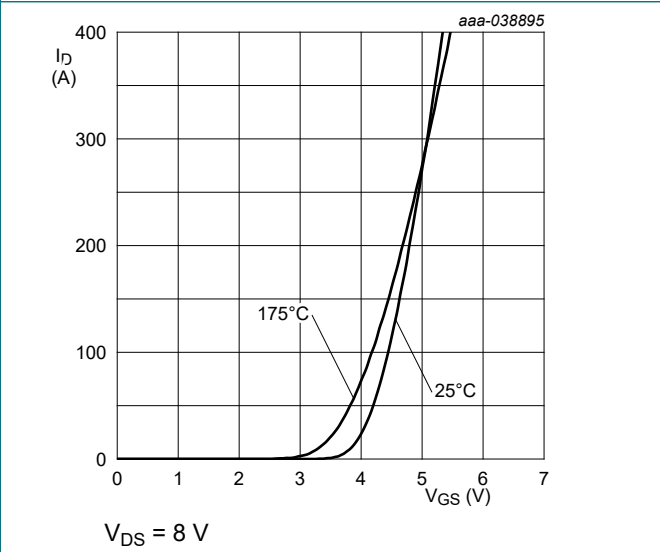


Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values

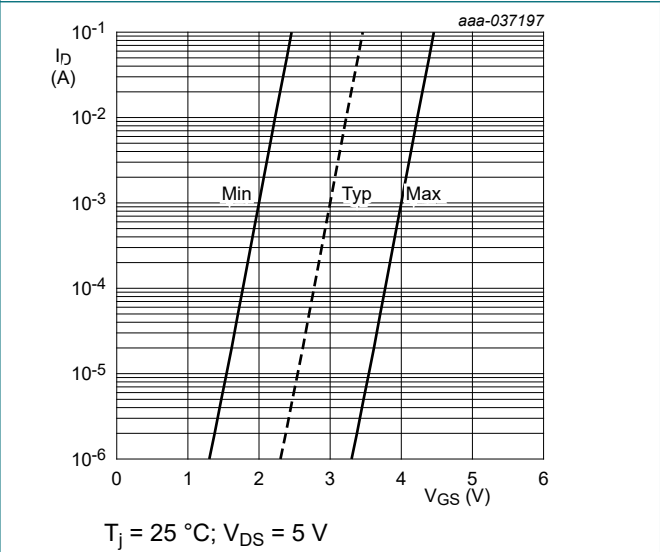


Fig. 11. Sub-threshold drain current as a function of gate-source voltage



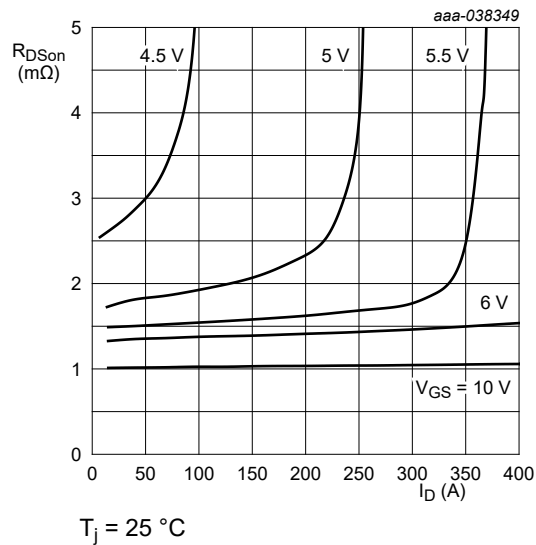


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

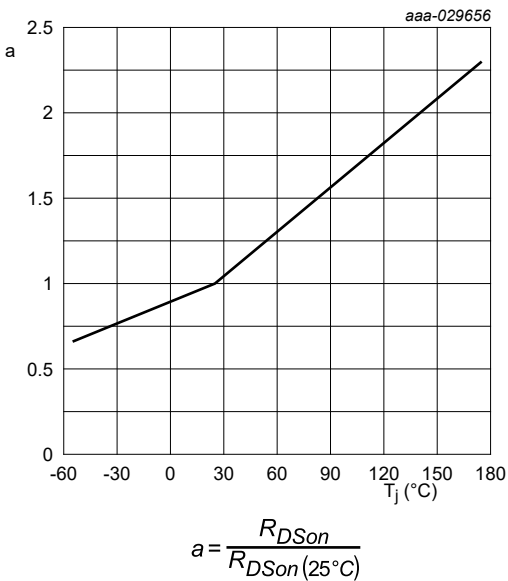


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

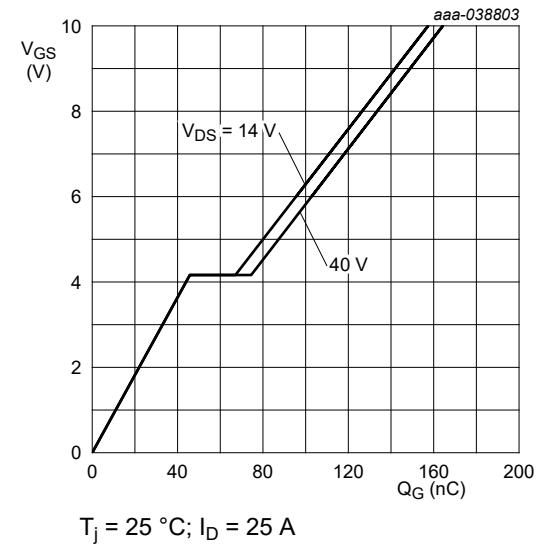


Fig. 14. Gate-source voltage as a function of gate charge; typical values

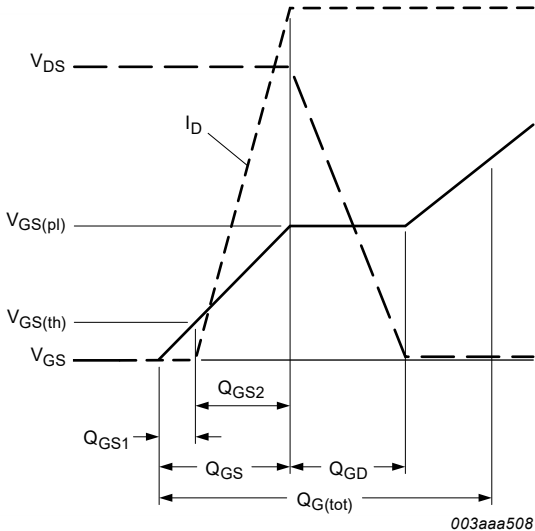


Fig. 15. Gate charge waveform definitions

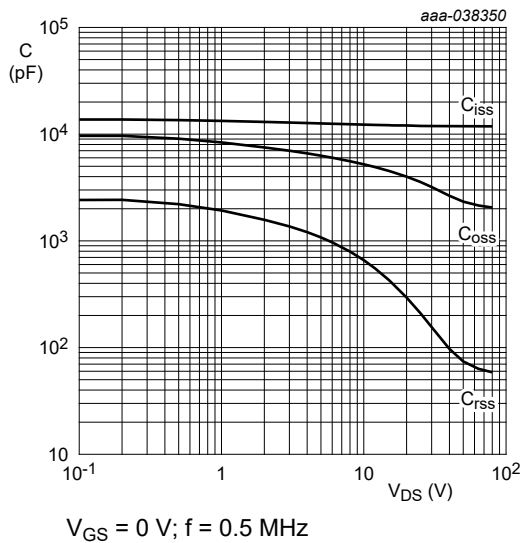


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

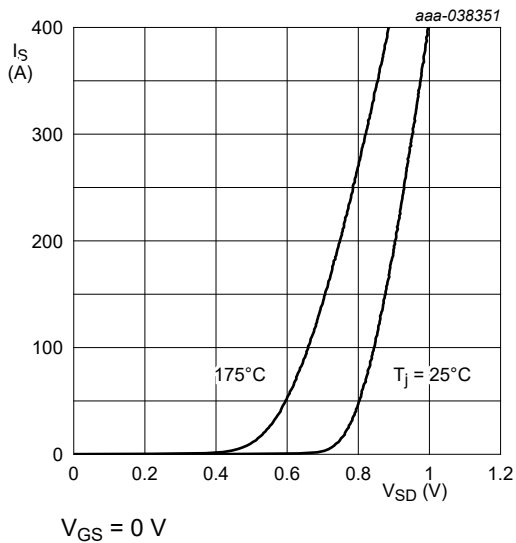


Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

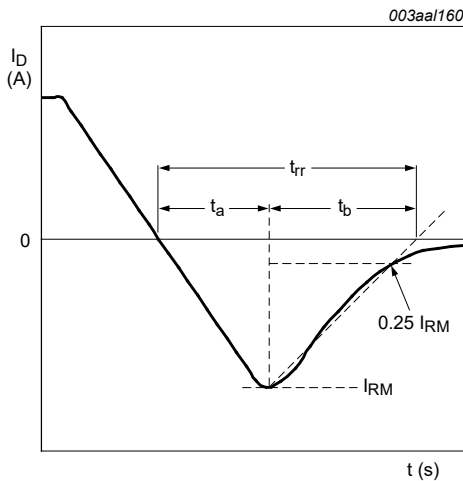
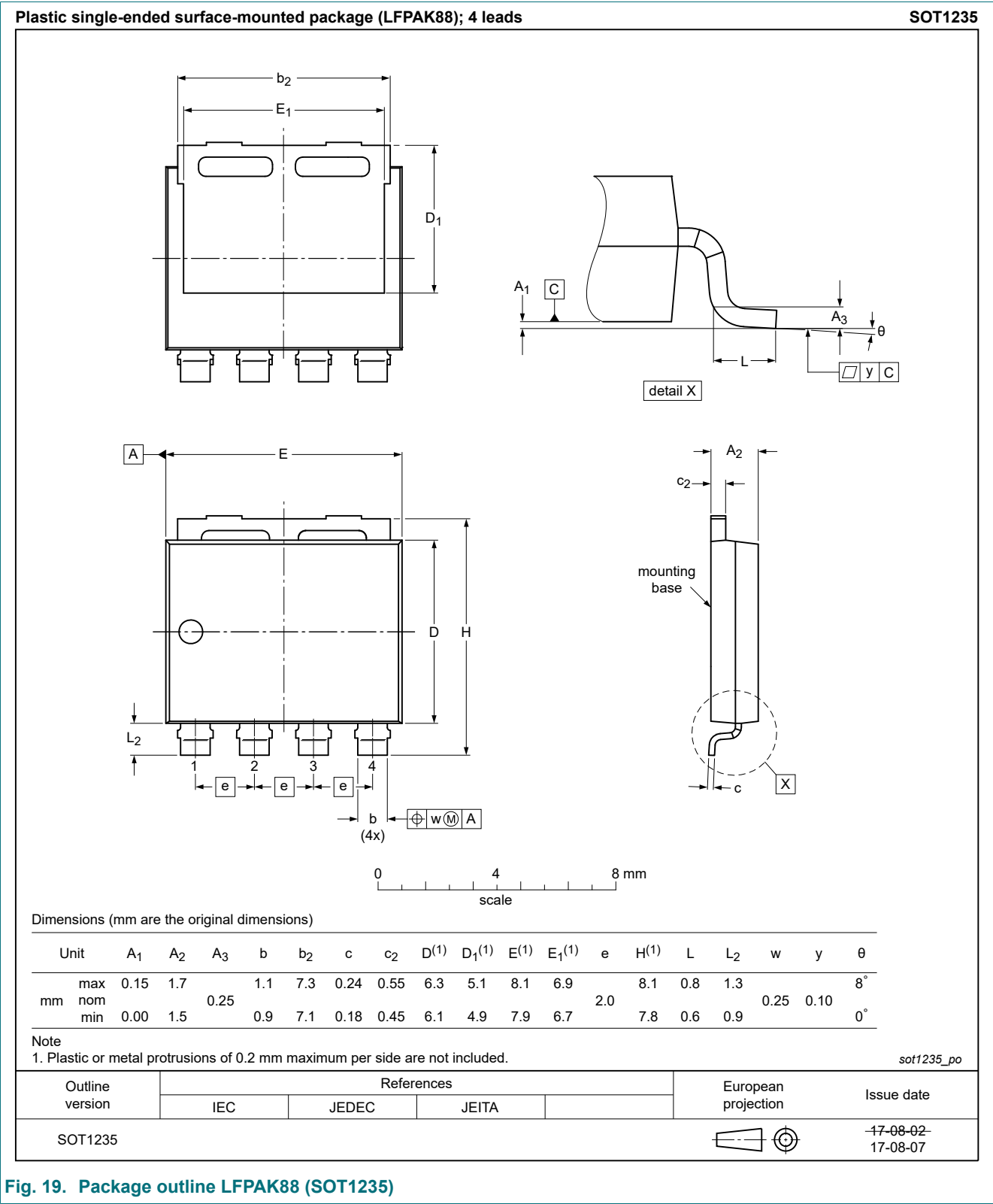
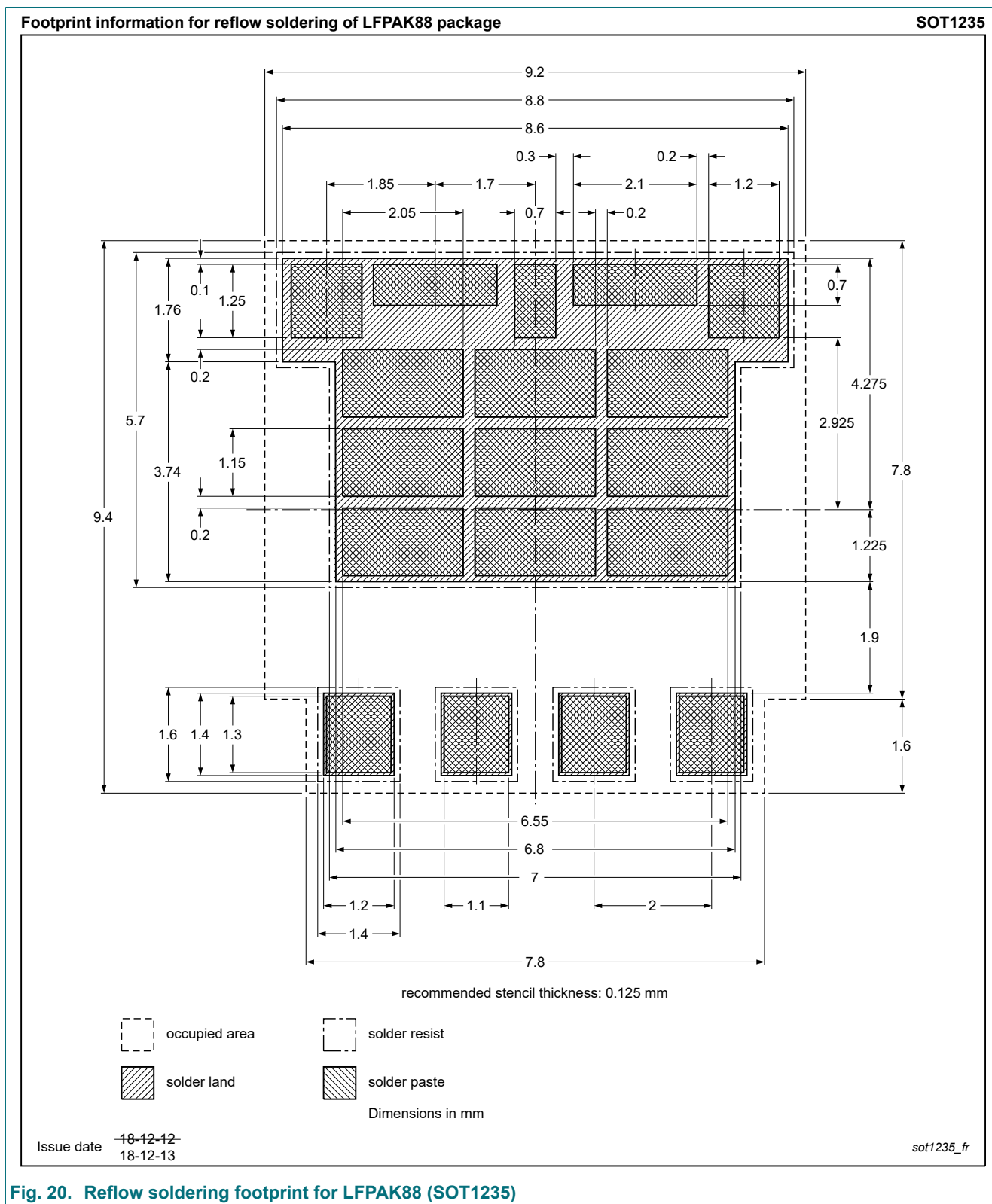


Fig. 18. Reverse recovery timing definition

11. Package outline



## 12. Soldering



**Fig. 20. Reflow soldering footprint for LPAK88 (SOT1235)**

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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